

ABSTRACT

COMPOSITION FOR FORMING ETCHING STOPPER LAYER

5 An object of the present invention is to provide a composition for
formation of etching stopper layer, which can simultaneously realize dry
etching selectivity and low permittivity, and a production process of a
semiconductor device using the same. This object can be attained by a
composition for formation of etching stopper layer, comprising a
10 silicon-containing polymer, the silicon-containing polymer contained in
the composition comprising a disilylbenzene structure, and a production
process of a semiconductor device comprising forming an etching
stopper layer using the composition.

Selected Drawing: Fig. 1